

General Description

The Sanrise SRC65R115BS is a high voltage power MOSFET, fabricated using advanced super junction technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and outstanding efficiency.

The SRC65R115BS break down voltage is 650V and it has a high rugged avalanche characteristics. The SRC65R115BS is available in PDFN8*8 package.

Symbol

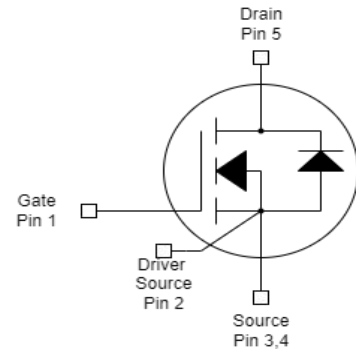
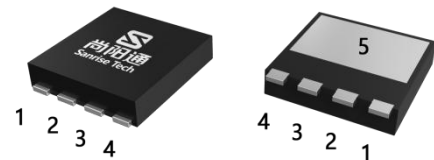


Figure 1 Symbol of SRC65R115BS

Package Type



PDFN8*8-4

Figure 2 Package Type of SRC65R115BS

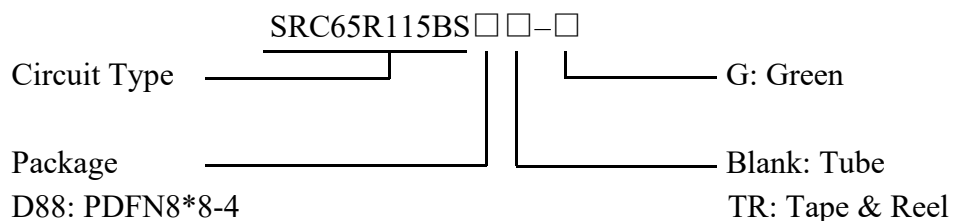
Features

- Ultra Low $R_{DS(ON)} = 115m\Omega @ V_{GS} = 10V$.
- $V_{ds}@T_{jmax}=700v$.
- Ultra Low Gate Charge, $Q_g=81nC$ typ.
- Intrinsic Fast-Recovery Body Diode
- Fast switching capability
- Robust design with better EAS performance
- Non-automotive Qualified
- Ultra-fast body diode

Application

- Server/ Telecom Power

Ordering Information



Package	Part Number	Marking ID	Packing Type
PDFN8*8-4	SRC65R115BSD88TR-G	SRC65R115BSD88G	Tape & Reel

115mΩ, 650V, Super Junction N-Channel Power MOSFET
SRC65R115BS
Absolute Maximum Ratings^{Note 1}

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage (static)		V_{GSS}	±20	V
Gate-Source Voltage (dynamic), AC ($f > 1$ Hz)		V_{GSS}	±30	V
Power Dissipation($T_C=25^{\circ}\text{C}$, TO-220C, TO-247, TO-263-2)		P_{tot}	231	W
Power Dissipation($T_C=25^{\circ}\text{C}$, TO-220F)		P_{tot}	31	W
Continuous Drain Current	$T_C=25^{\circ}\text{C}$	I_D	30	A
	$T_C=100^{\circ}\text{C}$		19	
	$T_C=125^{\circ}\text{C}$		13	
Pulsed Drain Current (Note 2)		I_{DM}	90	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	135	mJ
Avalanche Energy, Single Pulse (Note 4)		E_{AS}	1166	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	0.4	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	3.0	A
Continuous Diode Forward Current		I_S	30	A
Diode Pulse Current		$I_{S,PULSE}$	90	A
MOSFET dv/dt Ruggedness, $V_{DS} \leq 480\text{V}$		dv/dt	80	V/ns
Reverse Diode dv/dt, $V_{DS} \leq 480\text{V}$, $I_{SD} \leq I_D$		dv/dt	50	V/ns
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 to 150	$^{\circ}\text{C}$
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	$^{\circ}\text{C}$

Note:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $I_{AS}=2.0\text{A}$, $V_{DD}=60\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$. Finish goods test condition.
4. $I_{AS}=5.88\text{A}$, $V_{DD}=60\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$. Typical Eas.

Thermal characteristics

Parameter		Symbol	Min	Typ	Max	Unit
Thermal resistance, Junction-to-Case	PDFN8*8-4	R_{thJC}			0.54	$^{\circ}\text{C}/\text{W}$
Thermal resistance, Junction-to-Ambient	PDFN8*8-4	R_{thJA}			65	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics

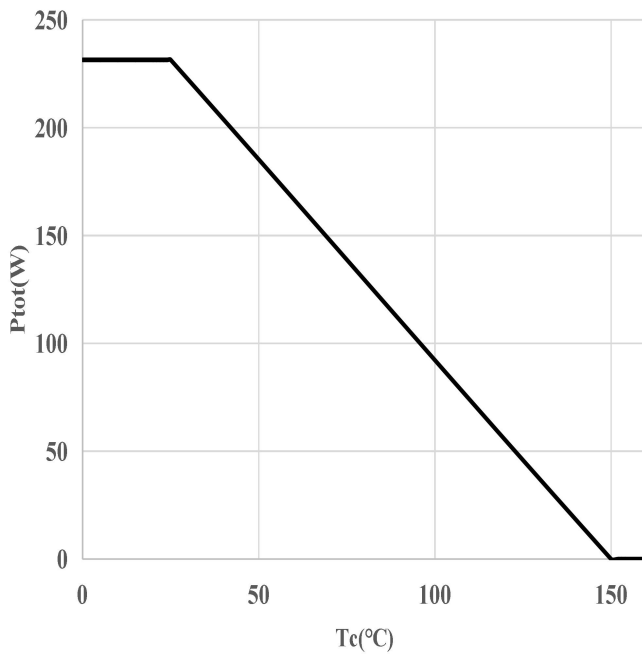
$T_J = 25^{\circ}\text{C}$, unless otherwise specified.

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250uA	650			V
Zero Gate Voltage Drain Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	uA
Gate-Body Leakage Current	Forward	I _{GSSF}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse	I _{GSSR}	V _{GS} =-30V, V _{DS} =0V			-100	
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =0.8mA	3.5	4.5	5.5	V
Static Drain-Source On-Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =16A		95	115	mΩ
Gate Resistance		R _G	f=1MHz, Open Drain		1.0		Ω
Dynamic Characteristics							
Input Capacitance		C _{ISS}	V _{DS} =400V, V _{GS} =0V, f=100KHz		1914		pF
Output Capacitance		C _{OSS}			54		pF
Effective output capacitance, energy related ^{NOTE5}		C _{O(er)}	V _{GS} =0V, V _{DS} =0...480V		80		pF
Effective output capacitance, time related ^{NOTE6}		C _{O(tr)}			630		
Turn-on Delay Time		t _{d(on)}	V _{DD} =400V, I _D =16A R _G =3Ω, V _{GS} =12V		37		ns
Rise Time		t _r			19		
Turn-off Delay Time		t _{d(off)}			50		
Fall Time		t _f			9		
Gate Charge Characteristics							
Gate to Source Charge		Q _{gs}	V _{DD} =400V, I _D =16A V _{GS} =0 to 10V		18		nC
Gate to Drain Charge		Q _{gd}			43		
Gate Charge Total		Q _g			81		
Gate Plateau Voltage		V _{plateau}			7.6		V
Reverse Diode Characteristics							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V, I _{SD} =16A		0.9	1.1	V
Reverse Recovery Time		t _{rr}	V _R =400V, I _F =16A dI _F /dt=100A/us		156		ns
Reverse Recovery Charge		Q _{rr}			1.86		uC
Peak Reverse Recovery Current		I _{rrm}			20		A

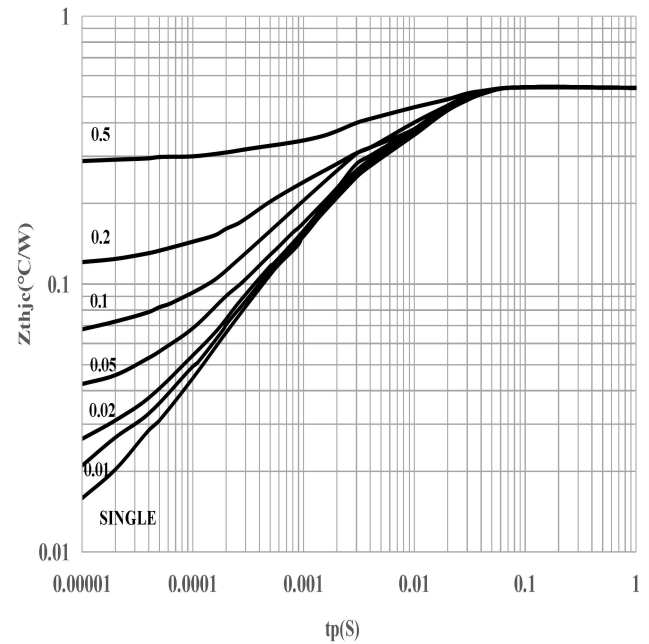
Note:

5. $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 480V

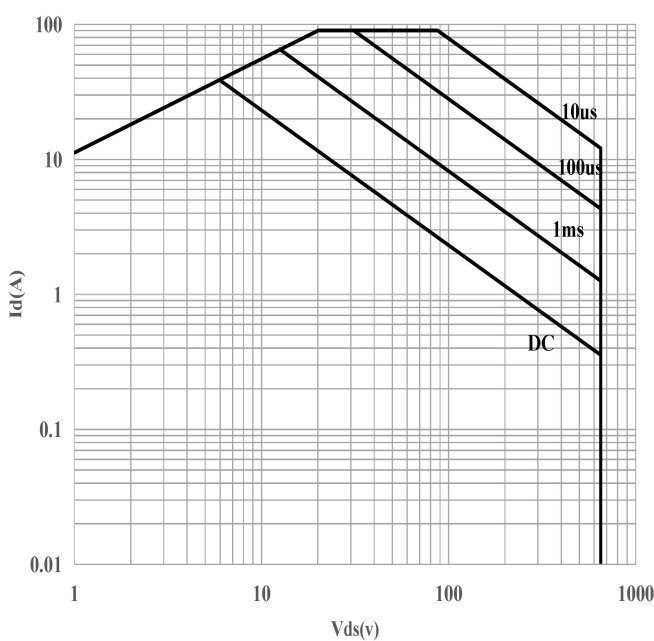
6. $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 480 V

Typical Performance Characteristics
Figure 3: Power Dissipation


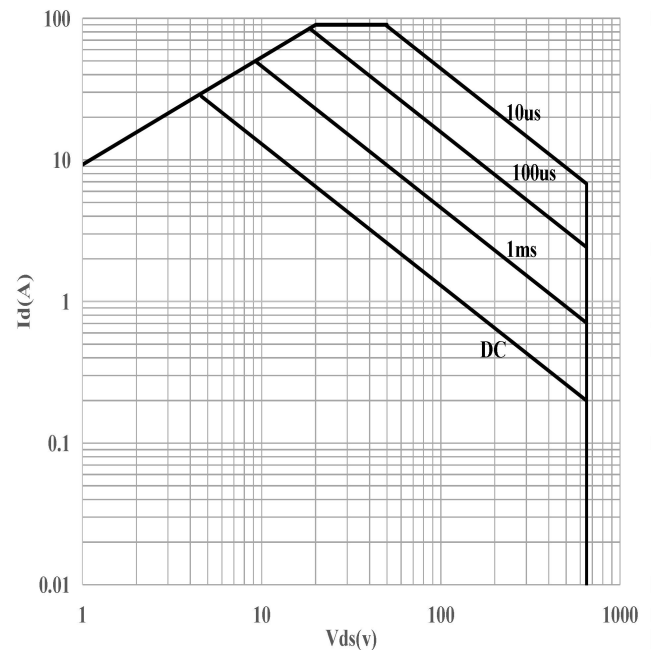
$$P_{tot} = f(T_c)$$

Figure 4: Max. Transient Thermal Impedance


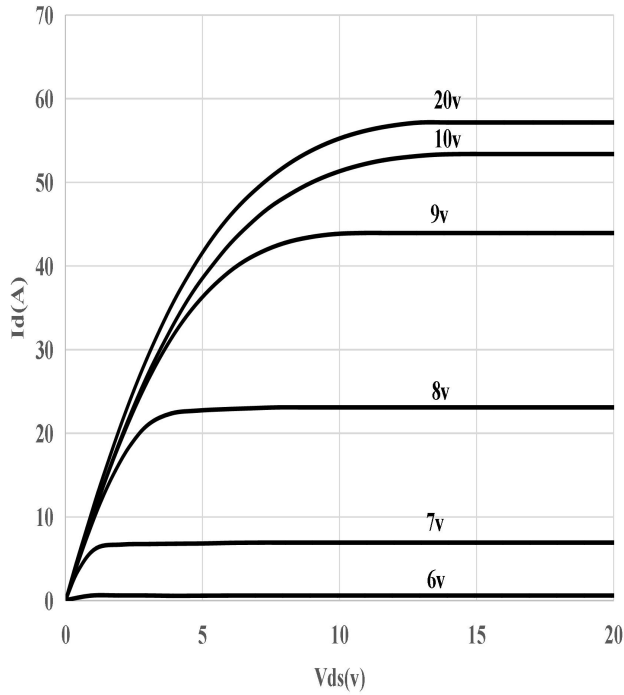
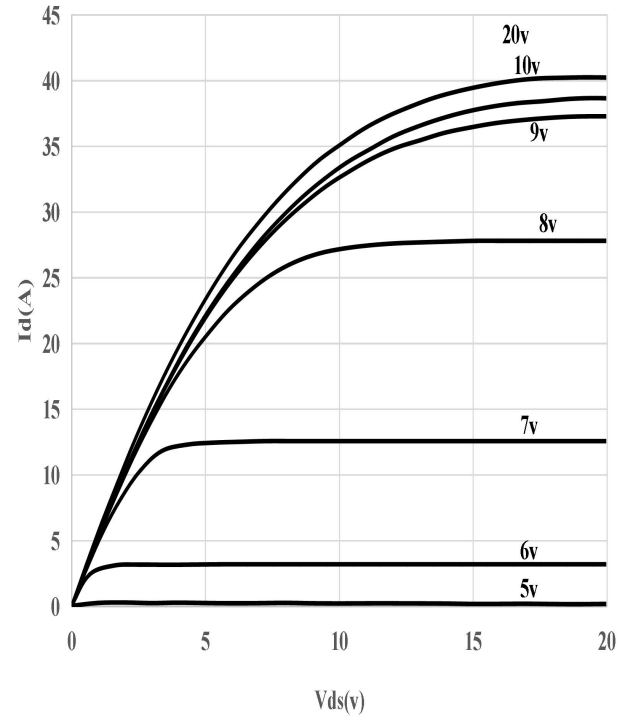
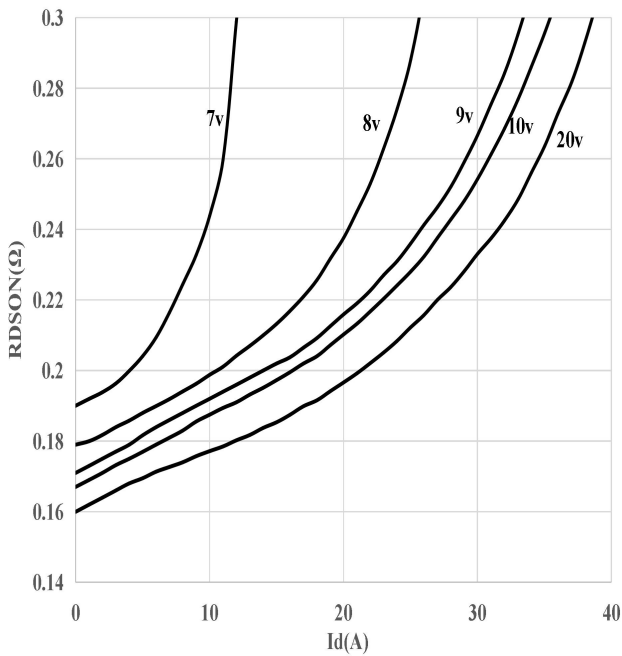
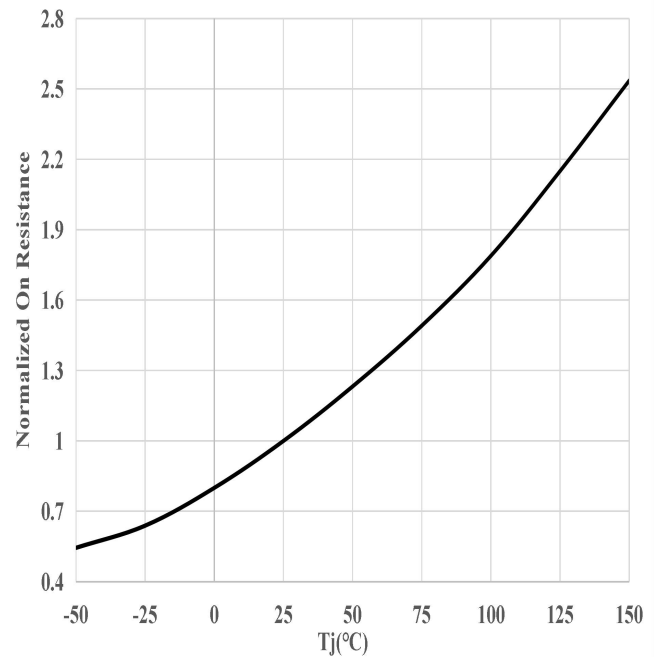
$$Z_{(th)JC} = f(t_p); \text{ parameter: } D = t_p/T$$

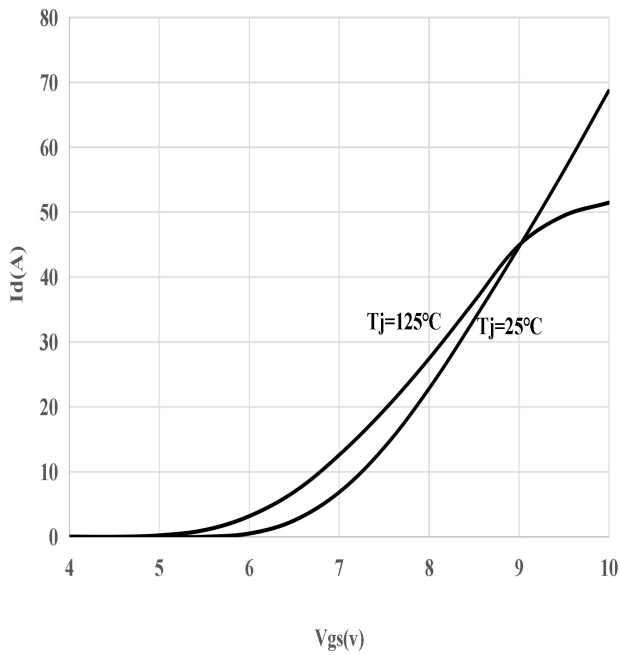
Figure 5: Safe Operating Area


$$I_D = f(V_{DS}); T_c = 25^\circ\text{C}; V_{GS} > 7\text{V}; \text{ parameter } t_p$$

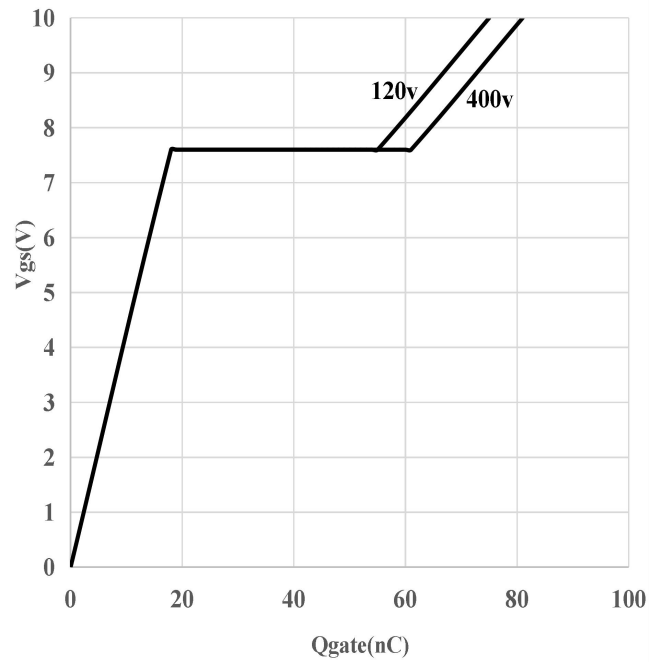
Figure 6: Safe Operating Area


$$I_D = f(V_{DS}); T_c = 80^\circ\text{C}; V_{GS} > 7\text{V}; \text{ parameter } t_p$$

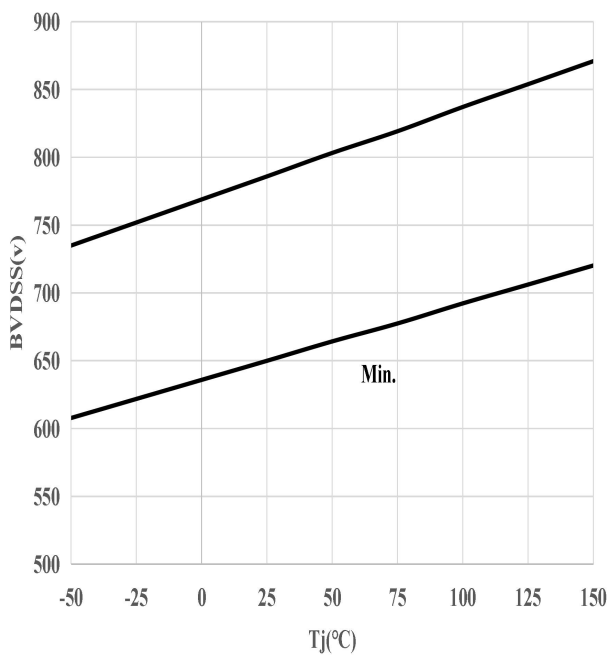
Figure 7: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 8: Typ. Output Characteristics

 $I_D = f(V_{DS}); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 9: Typ. Drain-Source On-State Resistance

 $R_{DS(on)} = f(I_D); T_j = 125^\circ\text{C}; \text{parameter: } V_{GS}$
Figure 10: Typ. Drain-Source On-State Resistance

 $R_{DS(on)} = f(T_j); I_D = 16\text{A}; V_{GS} = 10\text{V}$

115mΩ, 650V, Super Junction N-Channel Power MOSFET
SRC65R115BS
Figure 11: Typ. Transfer Characteristics


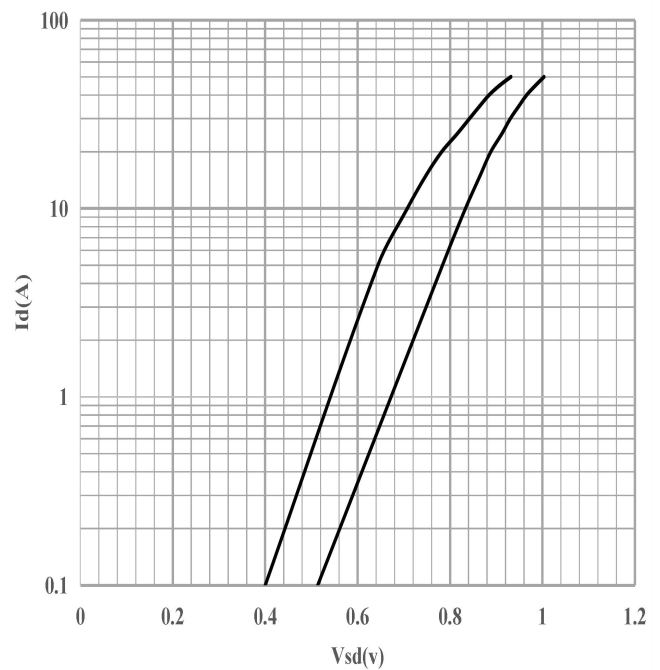
$$I_D = f(V_{GS}); V_{DS} = 20V$$

Figure 12: Typ. Gate Charge


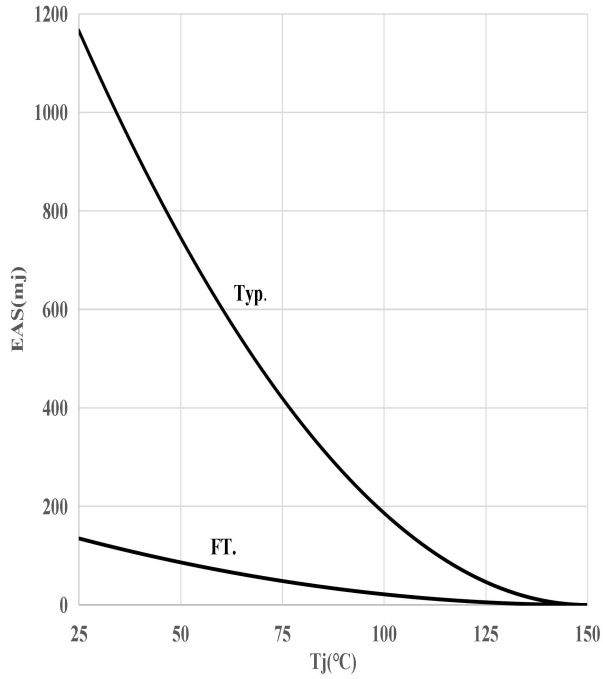
$$V_{GS} = f(Q_{gate}), I_D = 16A \text{ pulsed}$$

Figure 13: Drain-Source Breakdown Voltage


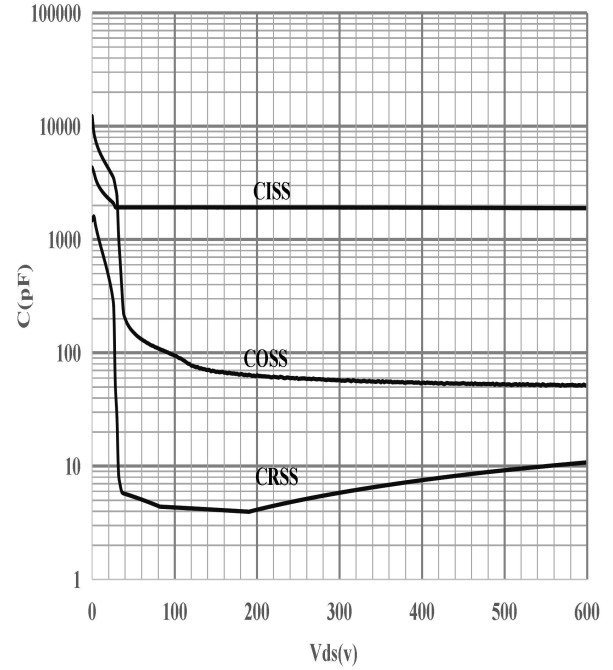
$$V_{BR(DSS)} = f(T_j); I_D = 10mA$$

Figure 14: Forward Characteristics of Reverse Diode


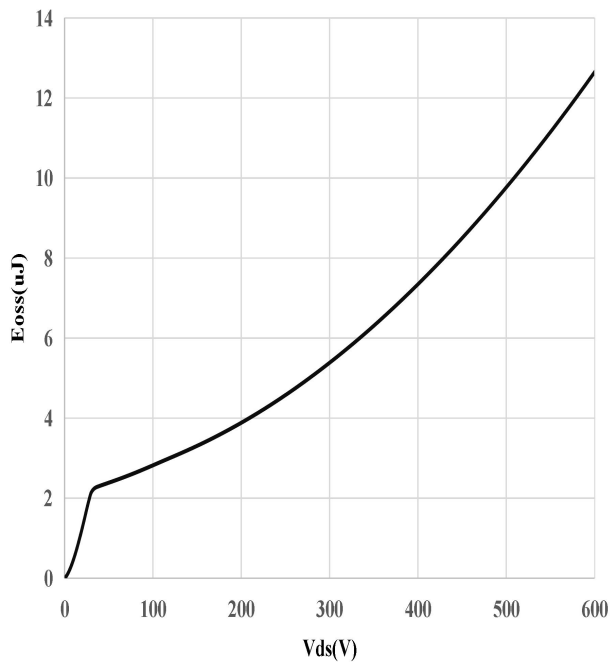
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Figure 15: Avalanche Energy


$$E_{AS}=f(T_j); V_{DD}=60V$$

Figure 16: Typ. Capacitances


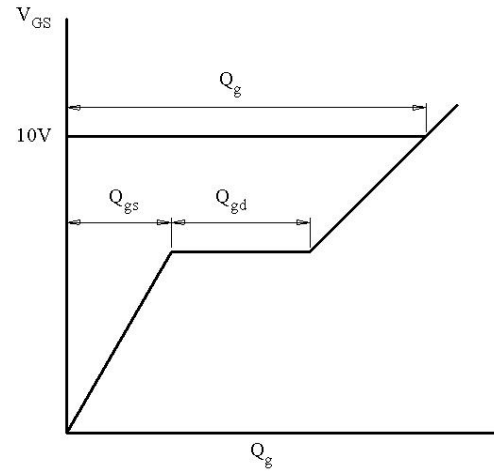
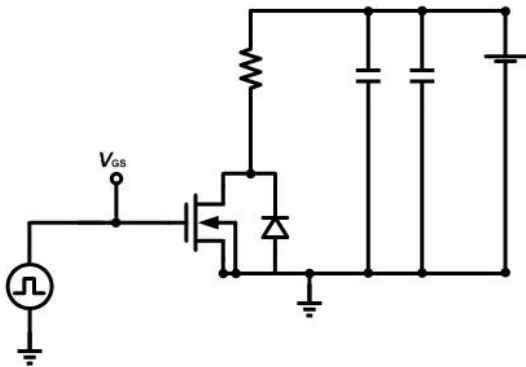
$$C=f(V_{DS}); V_{GS}=0; f=100KHz$$

Figure 17: Coss Stored Energy


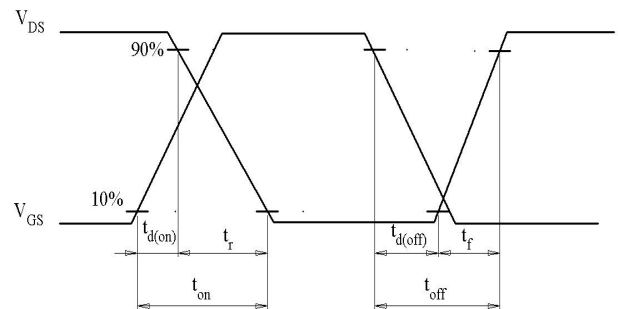
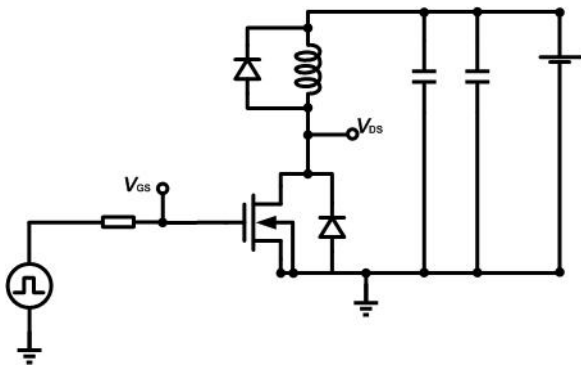
$$E_{oss}=f(V_{DS})$$

Test Circuits

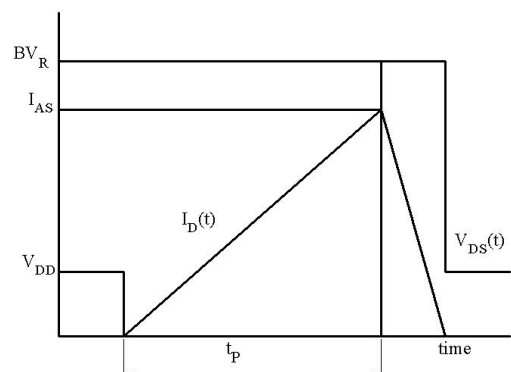
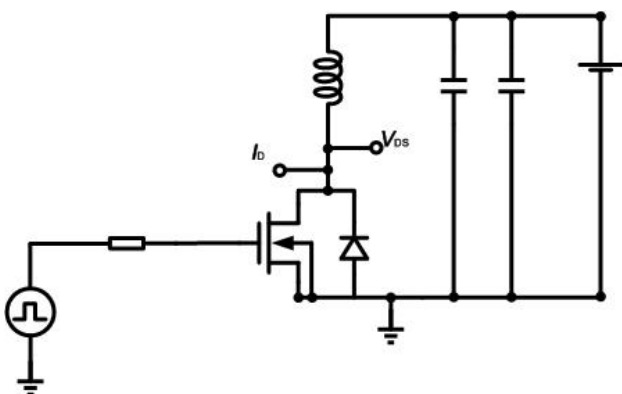
1. Gate Charge Test Circuit & Waveform



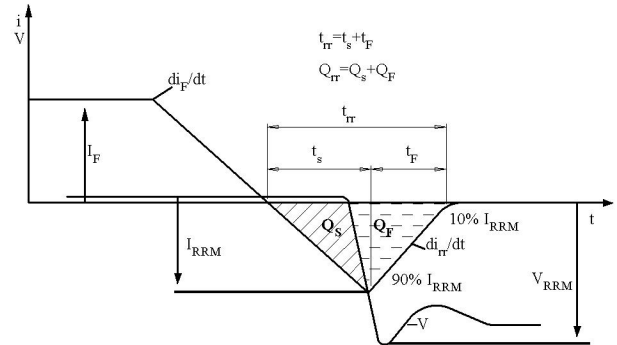
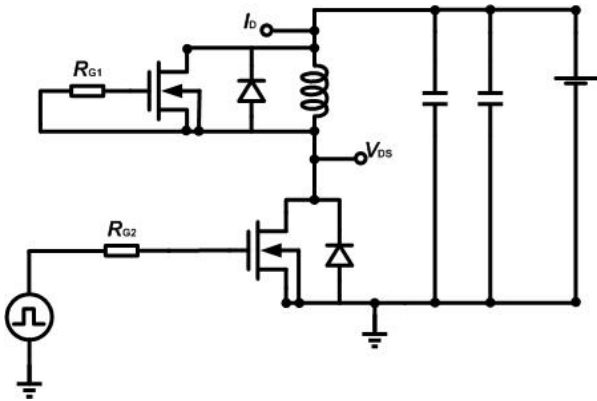
2. Switch Time Test Circuit

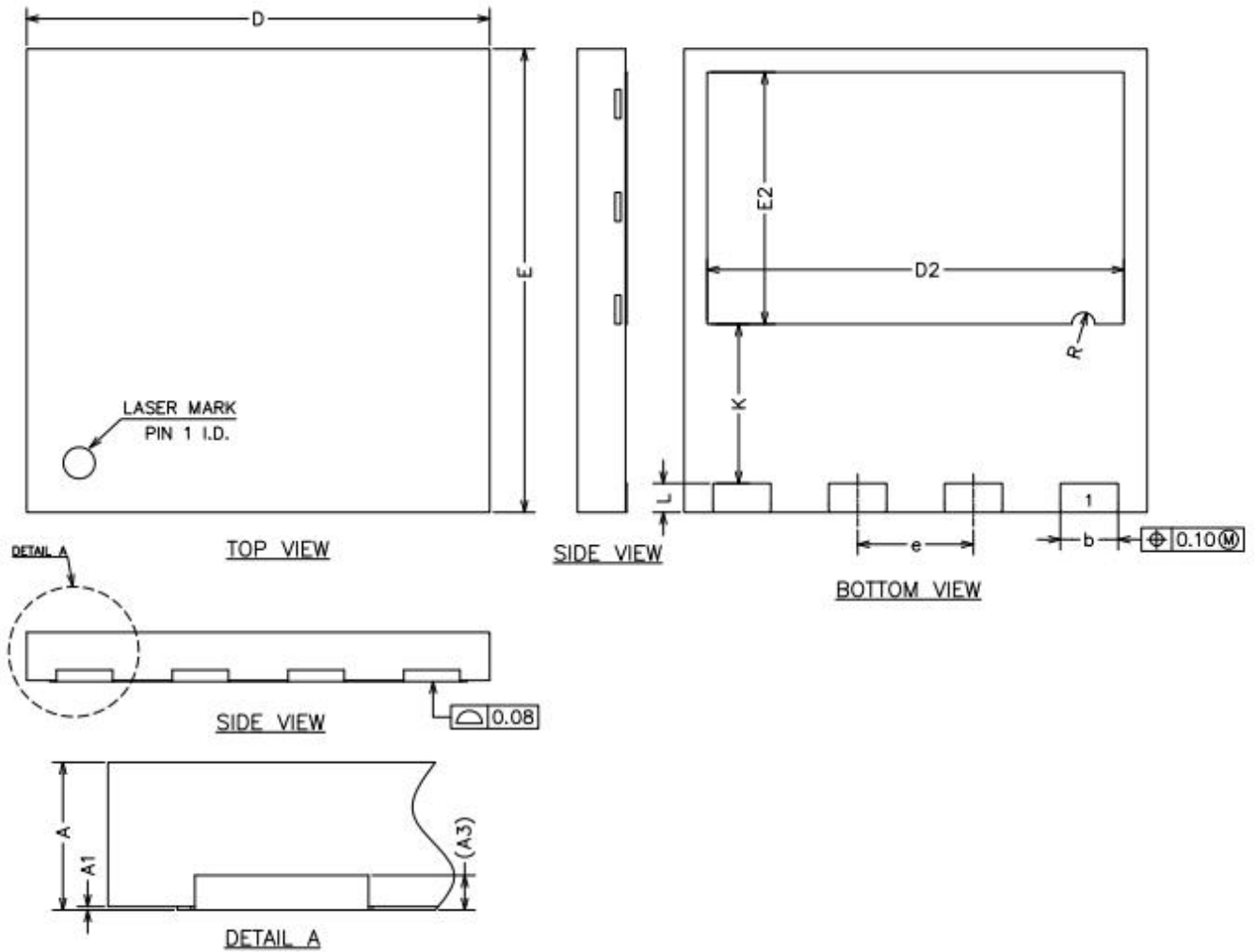


3. Unclaimed Inductive Switching Test Circuit & Waveforms



4. Test Circuit and Waveform for Diode Characteristics



Mechanical Dimensions
PDFN8*8-4
Unit: mm


Symbol	Dimensions(mm)			Symbol	Dimensions(mm)		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	0.80	0.85	0.90	D2	7.10	7.20	7.30
A1	0.00	0.02	0.05	E2	4.25	4.35	4.45
A3	-	0.20REF	-	e	1.90	2.00	2.10
b	0.90	1.00	1.10	K	2.65	2.75	2.85
D	7.90	8.00	8.10	L	0.40	0.50	0.60
E	7.90	8.00	8.10	R	-	0.20REF	-



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